NCE N-Channel Super Trench Power MOSFET

Description

The NCEP40T11K uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

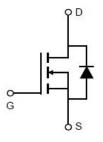
General Features

- V_{DS} =40V, I_D =110A $R_{DS(ON)}$ =2.4m Ω (typical) @ V_{GS} =10V $R_{DS(ON)}$ =3.3m Ω (typical) @ V_{GS} =4.5V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED! 100% ΔVds TESTED!



Schematic Diagram



Marking and pin assignment



TO-252 -2L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity		
NCEP40T11K	NCEP40T11K	TO-252-2L	_	_	-		

Absolute Maximum Ratings (T_c=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	40	V
Gate-Source Voltage	V _G s	±20	V
Drain Current-Continuous	I _D	110	Α
Drain Current-Continuous(Tc=100°C)	I _D (100°C)	85	Α
Pulsed Drain Current	I _{DM}	440	Α
Maximum Power Dissipation	P _D	150	W
Derating factor		1	W/℃
Single pulse avalanche energy (Note 1)	Eas	500	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}$

NCEP40T11K

Thermal Characteristic

Thermal Resistance,Junction-to-Case	R _{eJC}	1.0	°C/W	
Thermal Resistance, Junction-to-Case	NθJC	1.0	[C/ v v	

Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	40		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.2	1.7	2.2	V
Davis Course On Otata Davistana	-	V _{GS} =10V, I _D =55A	-	2.4	3.5	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =55A	-	3.3	4.8	mΩ
Forward Transconductance	G FS	V _{DS} =5V,I _D =55A	-	60	-	S
Dynamic Characteristics			<u> </u>			
Input Capacitance	C _{lss}	V 00V/V 0V	-	3510	-	PF
Output Capacitance	Coss	V_{DS} =20V, V_{GS} =0V, F=1.0MHz	-	1050	-	PF
Reverse Transfer Capacitance	C _{rss}		-	60	-	PF
Switching Characteristics (Note 2)			<u> </u>			
Turn-on Delay Time	t _{d(on)}		-	10.5	-	nS
Turn-on Rise Time	t _r	V_{DD} =20 V , I_D =55 A	-	4	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =1.6 Ω	-	35	-	nS
Turn-Off Fall Time	t _f		-	5	-	nS
Total Gate Charge	Qg	\/ 00\/ L FFA	-	60	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =20V,I _D =55A, V _{GS} =10V	-	9.9	-	nC
Gate-Drain Charge	Q_{gd}		-	9.5	-	nC
Drain-Source Diode Characteristics	, ,		•			
Diode Forward Voltage	V _{SD}	V _{GS} =0V,I _S =55A	-		1.2	V
Diode Forward Current	Is		-	-	110	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = I _S	-		24	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs	-		68	nC

Notes:

^{2.}Guaranteed by design, not subject to production

^{3.}These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsin k, assuming a maximum junction temperature of TJ(MAX)=175° C. The SOA curve provides a single pulse rating.

Typical Electrical and Thermal Characteristics

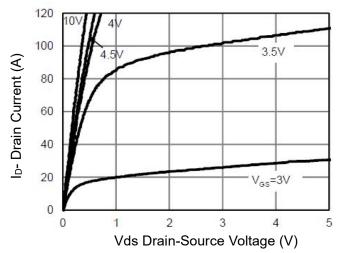


Figure 1 Output Characteristics

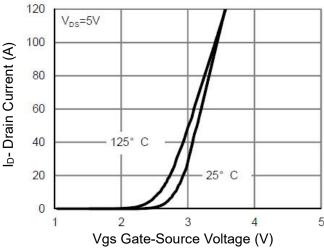


Figure 2 Transfer Characteristics

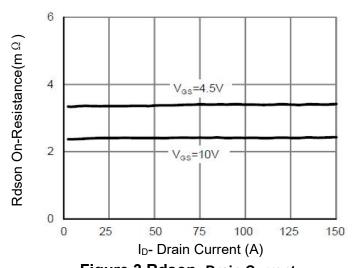


Figure 3 Rdson- Drain Current

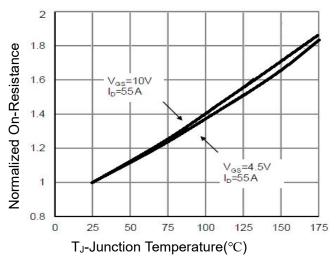


Figure 4 Rdson-JunctionTemperature

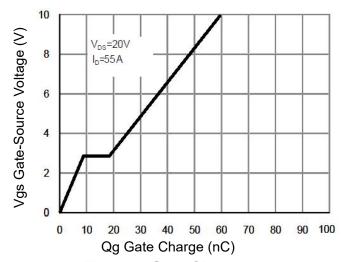


Figure 5 Gate Charge

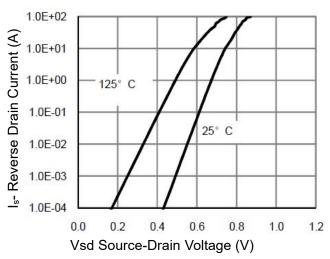


Figure 6 Source- Drain Diode Forward

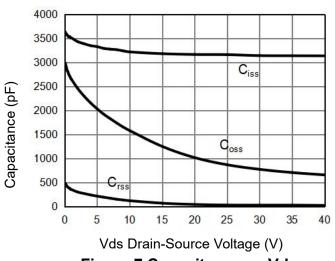


Figure 7 Capacitance vs Vds

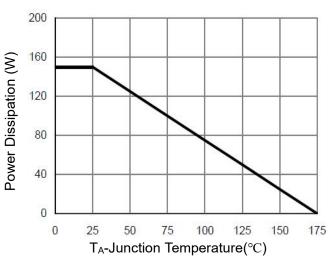


Figure 9 Power De-rating

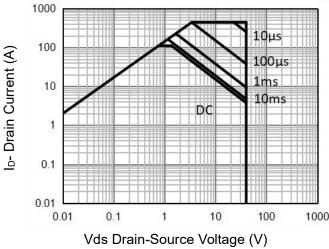


Figure 8 Safe Operation Area (Note 3)

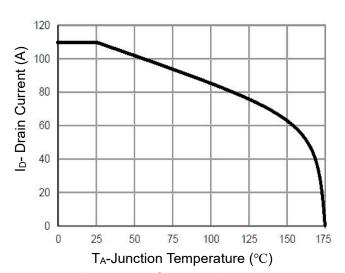


Figure 10 Current De-rating

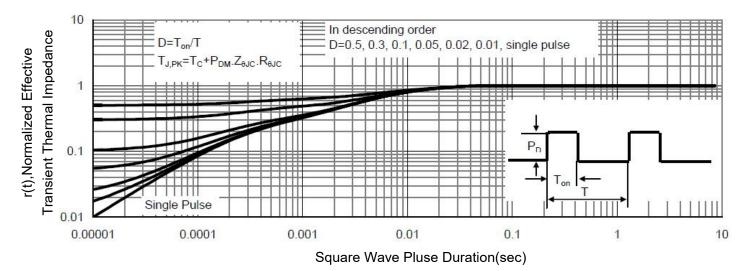
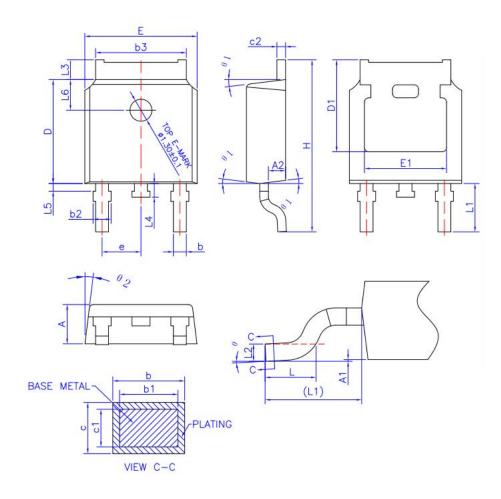


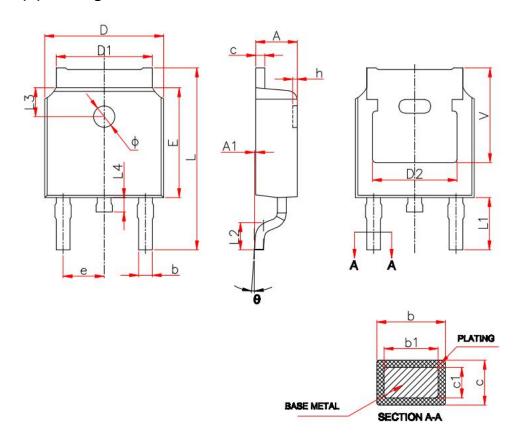
Figure 11 Normalized Maximum Transient Thermal Impedance

TO-252-2L(P) Package Information



SYMBOL	MIN	NOM	MAX	
Α	2.20	2.30	2.38	
A1	0		0.10	
A2	0.90	1.01	1.10	
b	0.72		0.85	
b1	0.71	0.76	0.81	
b2	0.72		0.90	
b3	5.13	5.33	5.46	
c	0.47		0.60	
c1	0.46	0.51	0.56	
c2	0.47		0.60	
D	6.00	6.10	6.20	
D1	5.25			
E	6.50	6.60	6.70	
E1	4.70			
е	2.186	2.286	2.386	
H	9.80	10.10	10.40	
L	1.40	1.50	1.70	
L1	2.90 REF			
L2	0.508 BSC			
L3	0.90		1.25	
L4	0.60	0.80	1.00	
L5	0.15		0.75	
L6	1.80 REF			
θ	0°		8°	
01	5°	7°	9°	
θ2	5°	7°	90	

TO-252-2L(E) Package Information



Symbol	Millin	neters
Symbol	Min.	Max.
Α	2.20	2.40
A1	0.00	0.13
b	0.66	0.86
b1	0.73	0.79
С	0.46	0.58
c1	0.50	0.52
D	6.50	6.70
D1	5.10	5.46
D2	4.83	REF.
E	6.00	6.20
е	2.19	2.39
L	9.80	10.40
L1	2.90	REF.
L2	1.40	1.70
L3	1.60 REF.	
L4	0.60	1.00
Ф	1.10	1.30
θ	0°	8°

NCEP40T11K

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